

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI TVV030A is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	16 A
<b>V<sub>CB0</sub></b>	60 V
<b>V<sub>CEO</sub></b>	30 V
<b>V<sub>EBO</sub></b>	4.0 V
<b>P<sub>DISS</sub></b>	150 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	1.2 °C/W

**PACKAGE STYLE .500 4L STUD(A)**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		1.050 / 26.67
C	.545 / 13.84	.555 / 14.10
D	.495 / 12.57	.505 / 12.83
E	.003 / 0.08	.007 / 0.18
F		.830 / 21.08
G	.185 / 4.70	.198 / 5.03
H	.497 / 12.62	.530 / 13.46

**ORDER CODE: ASI10661**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CB0</sub></b>	I <sub>C</sub> = 100 mA	60			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 100 mA      R <sub>BE</sub> = 10 Ω	60			<b>V</b>
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 100 mA	30			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	4.0			<b>V</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 1.0 A	10		120	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 30 V      f = 1.0 MHz			150	<b>pF</b>
<b>P<sub>G</sub></b>	V <sub>CE</sub> = 28 V      I <sub>C</sub> = 3.5 A      f = 225 MHz	7.5			<b>dB</b>
<b>IMD<sub>1</sub></b>	P <sub>OUT</sub> = 30 W	-53			<b>dBc</b>